

HIGH VOLTAGE FASTSWITCHING NPN POWER TRANSISTOR

- HIGH VOLTAGE CAPABILITY
- VERY HIGH SWITCHING SPEED
- LOW BASE-DRIVE REQUIREMENTS

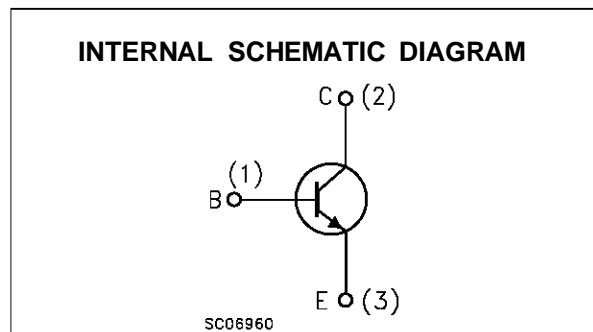
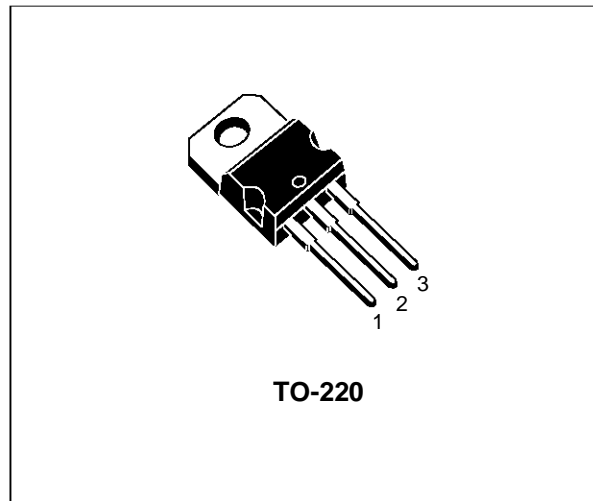
APPLICATIONS:

- SWITCH MODE POWER SUPPLIES
- HORIZONTAL DEFLECTION FOR COLOUR TVS AND MONITORS

DESCRIPTION

The SGSF344 is manufactured using Multi-epitaxial Mesa technology for cost-effective high performance and uses a Hollow Emitter structure to enhance switching speeds.

The SGSF series is designed for high speed switching applications such as power supplies and horizontal deflection circuits in TVs and monitors.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	1200	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	600	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	7	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	12	A
I_B	Base Current	5	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	8	A
P_{tot}	Total Dissipation at $T_c = 25$ °C	85	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

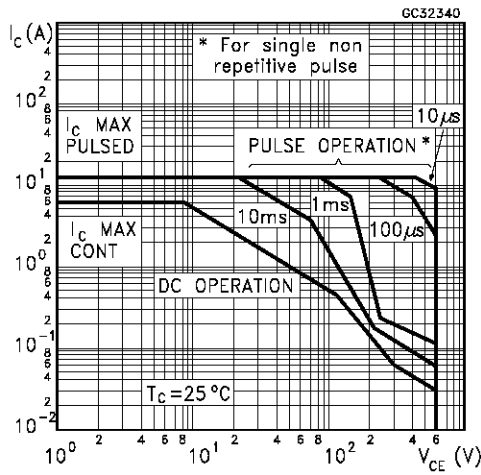
R _{thj-case}	Thermal Resistance Junction-case	Max	1.5	°C/W
-----------------------	----------------------------------	-----	-----	------

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

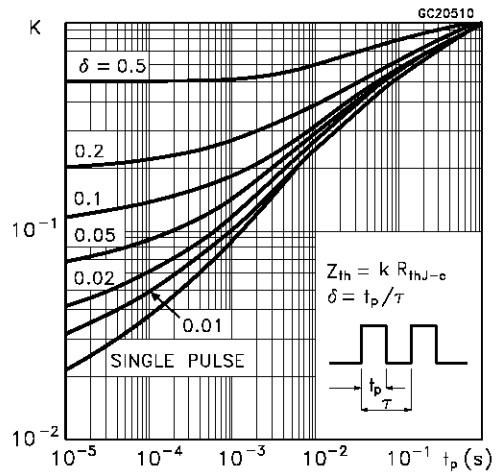
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1200 V			200	μA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{EC} = 380 V V _{EC} = 600 V			200 2	μA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{BE} = 7 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 100 mA	600			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 3.5 A I _B = 0.7 A I _C = 2.5 A I _B = 0.35 A			1.5 1.5	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 3.5 A I _B = 0.7 A I _C = 2.5 A I _B = 0.35 A			1.5 1.5	V V
t _{ON} t _s t _f	Turn-on Time Storage Time Fall Time	RESISTIVE LOAD V _{CC} = 250 v I _C = 3.5 A I _{B1} = 0.7 A I _{B1} = -1.4 A		0.7 2.2 0.18	1.2 3.5 0.4	μs μs μs
t _{ON} t _s t _f	Turn-on Time Storage Time Fall Time	RESISTIVE LOAD V _{CC} = 250 v I _C = 3.5 A I _{B1} = 0.7 A I _{B1} = -1.4 A With Antisaturation Network		0.7 1.5 0.2		μs μs μs
t _{ON} t _s t _f	Turn-on Time Storage Time Fall Time	RESISTIVE LOAD V _{CC} = 250 V I _C = 3.5 A I _{B1} = 0.7 A V _{BE(off)} = -5 V		0.7 1 0.2		μs μs μs
t _s t _f	Storage Time Fall Time	INDUCTIVE LOAD I _C = 3.5 A h _{FE} = 5 V _{CL} = 450 V V _{BE(off)} = -5 V L = 300 μH R _{BB} = 1.2 Ω		1.4 0.1	2.8 0.2	μs μs
t _s t _f	Storage Time Fall Time	INDUCTIVE LOAD I _C = 3.5 A h _{FE} = 5 V _{CL} = 450 V V _{BE(off)} = -5 V L = 300 μH R _{BB} = 1.2 Ω T _c = 100 °C			4 0.3	μs μs

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

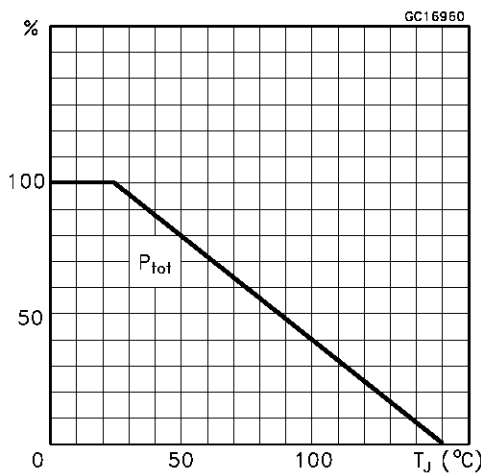
Safe Operating Area



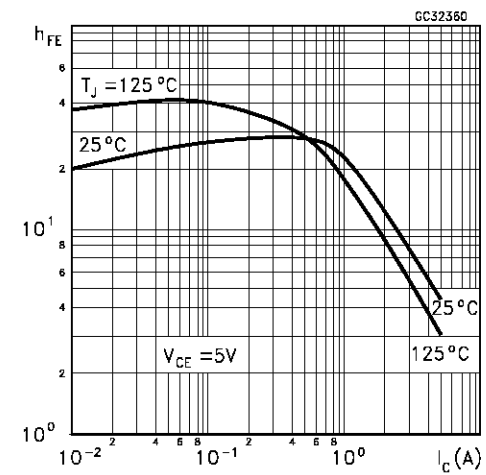
Thermal Impedance



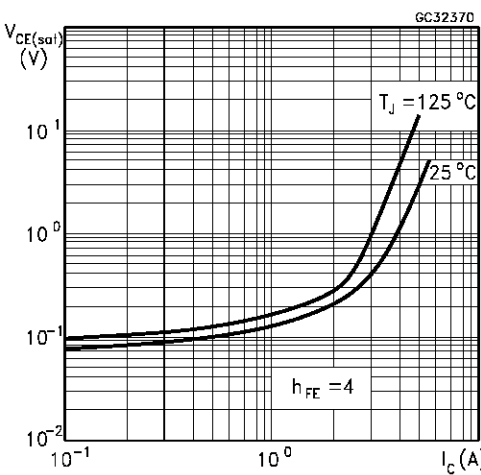
Derating Curve



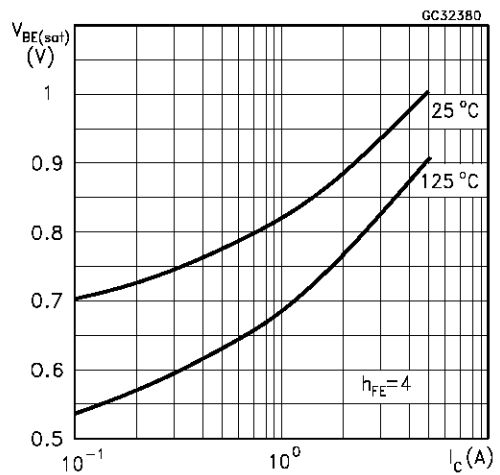
DC Current Gain



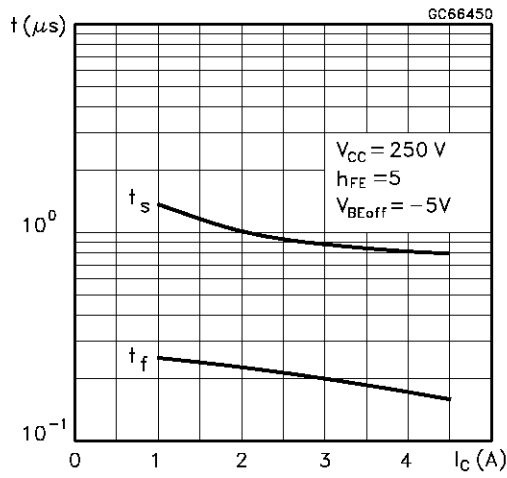
Collector Emitter Saturation Voltage



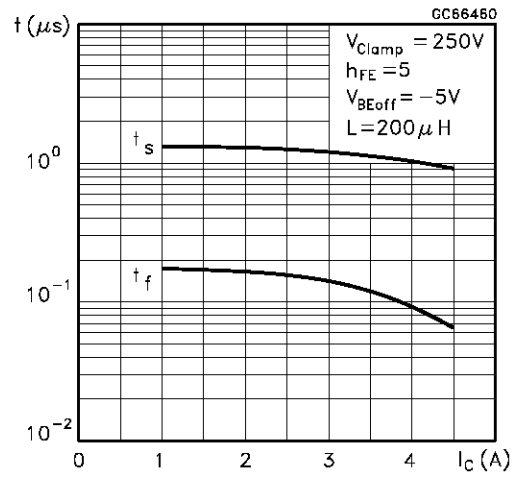
Base Emitter Saturation Voltage



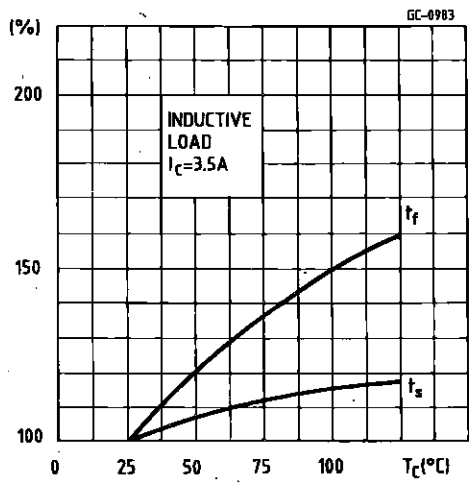
Resistive Load Switching Times



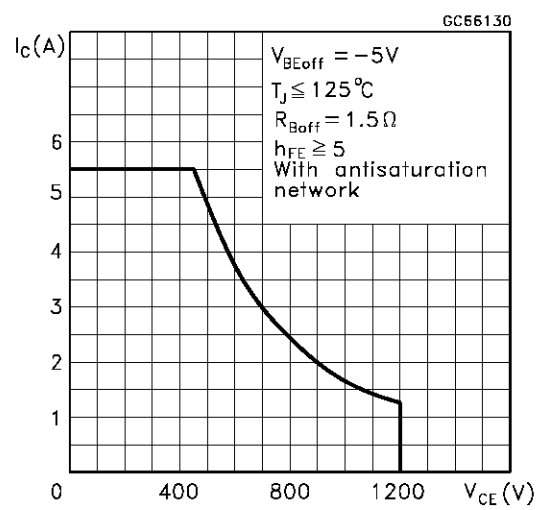
Inductive Load Switching Times



Switching Times Percentance Variation

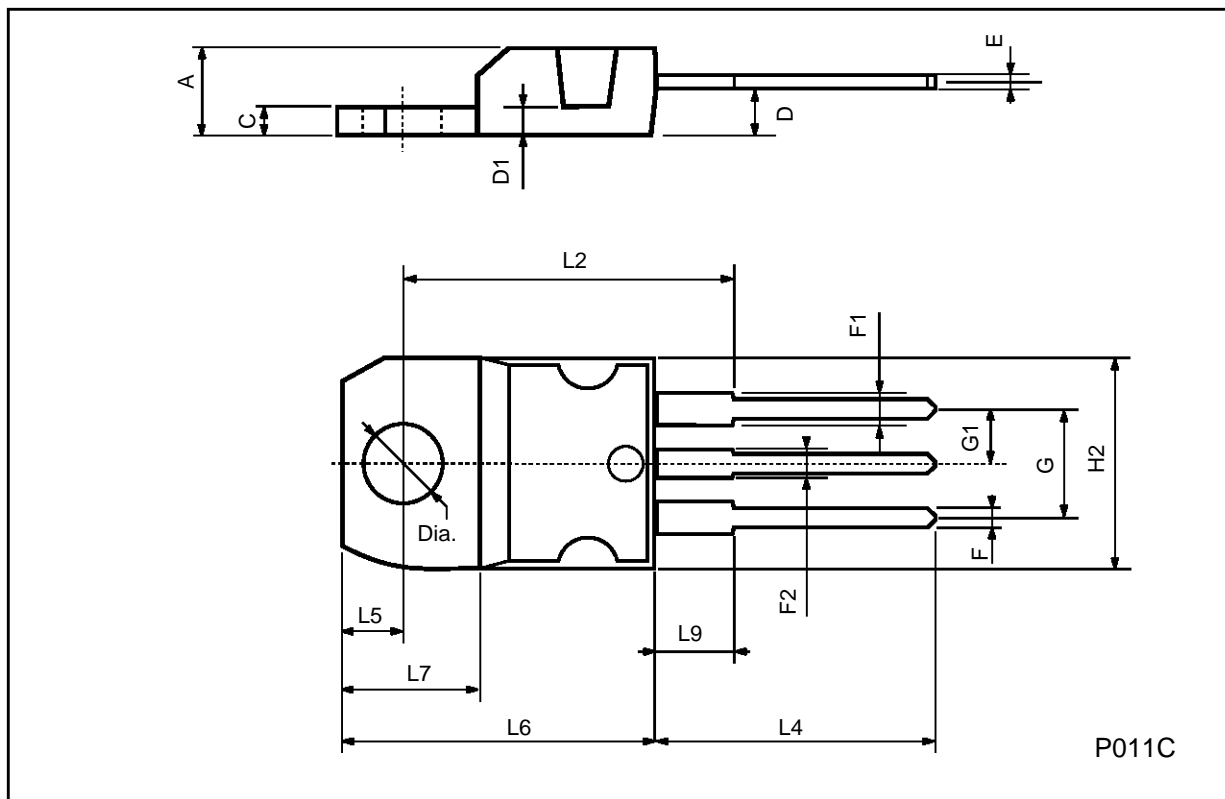


Reverse Biased SOA



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1997 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A

...